

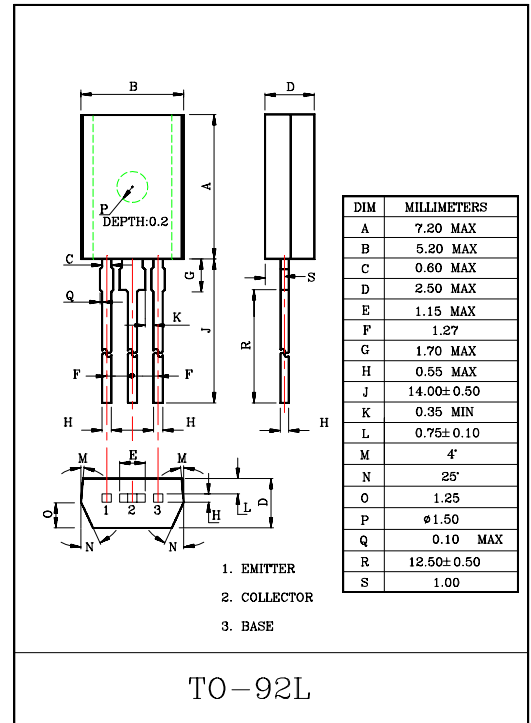
HIGH CURRENT APPLICATION.

FEATURES

- Complementary to KTC3205.

MAXIMUM RATINGS (Ta=25°C)

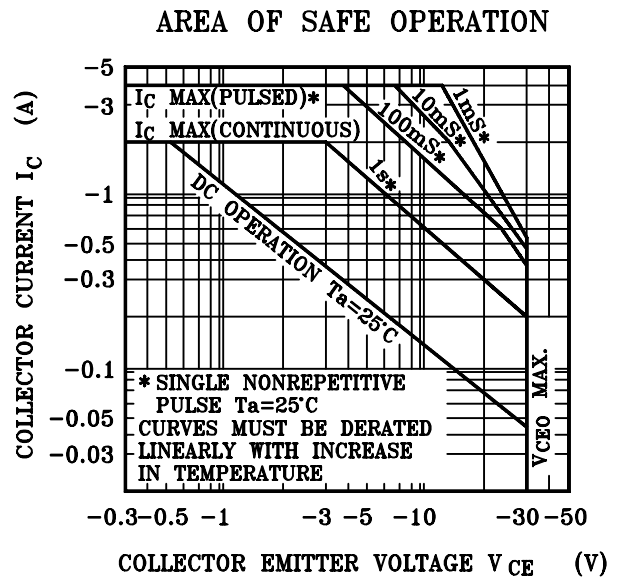
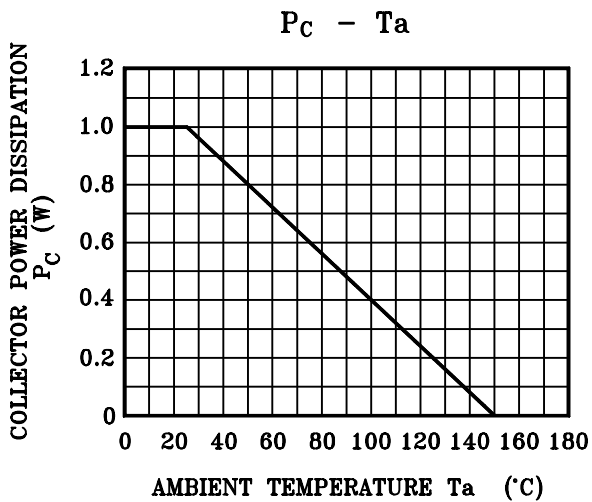
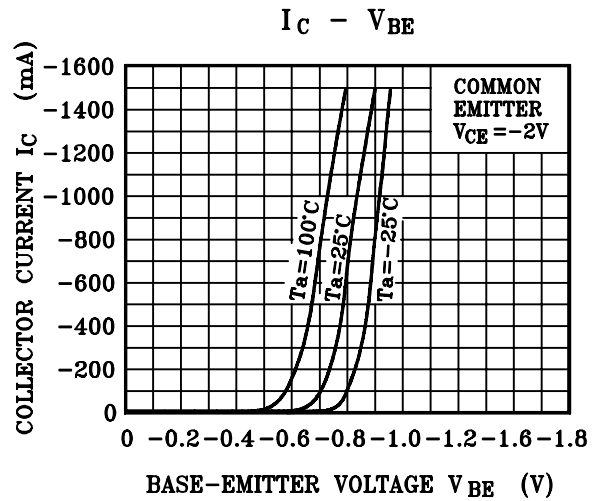
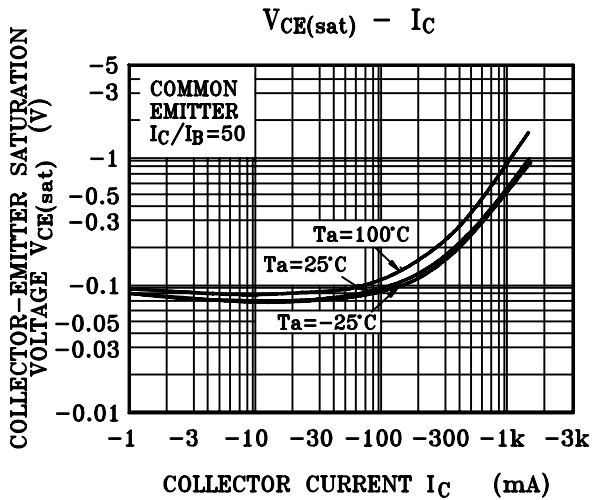
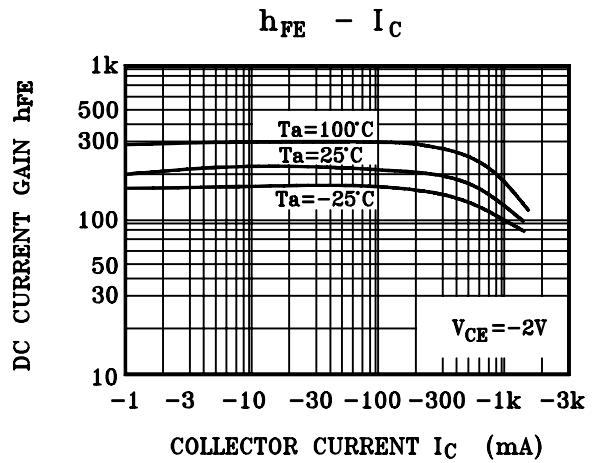
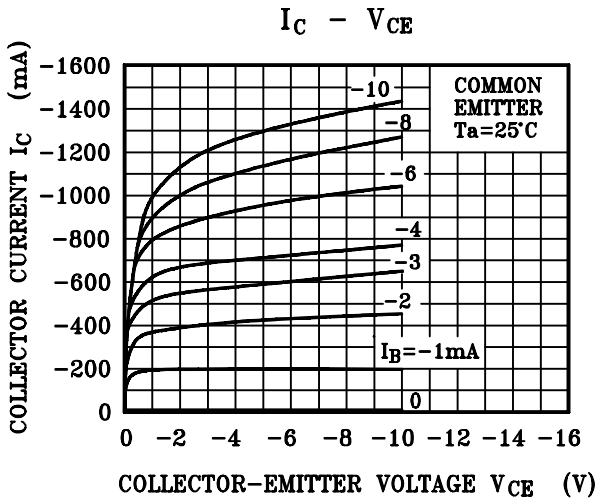
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Emitter Current	I_E	2	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C=-1mA, I_C=0$	-5	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=-2V, I_C=-500mA$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-0.03A$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-2V, I_C=-500mA$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE}=-2V, I_C=-500mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	48	-	pF

Note : $h_{FE}(1)$ Classification 0:100~200, Y:160~320



SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

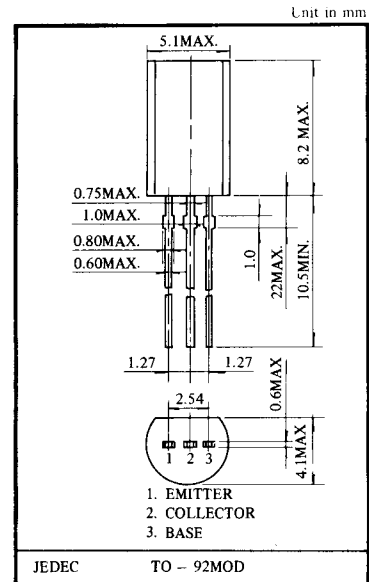
2SA1273

APPLICATIONS

- Audio Power Amplifier Applications.

FEATURES

- Complementary to 2SC 3205 and 3 Watts Output Applications.



MAXIMUM RATINGS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V	Emitter Current	I_E	2	A
Collector-Emitter Voltage	V_{CEO}	-30	V	Collector Dissipation	P_C	1	W
Emitter-Base Voltage	V_{EBO}	-5	V	Junction Temperature	T_j	150	°C
Collector Current	I_C	-2	A	Storage Temperature	T_{stg}	-55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -500mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	48	-	pF

NOTE: According to h_{FE} , Classified as follows.

0	100-200	Y	160-320
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